

2SK4208

Silicon N-channel enhancement MOS FET

For high speed switching circuits

■ Features

- Gate-source surrender voltage $V_{GSS} : \pm 30$ V guaranteed
- Avalanche energy capability guaranteed: $EAS > 801$ mJ
- High-speed switching: $t_f = 88$ ns (typ.)

■ Absolute Maximum Ratings $T_C = 25^\circ C$

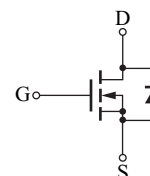
Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	V_{DSS}	200	V
Gate-source surrender voltage	V_{GSS}	± 30	V
Drain current	I_D	± 30	A
Peak drain current *	I_{DP}	± 160	A
Avalanche energy capability	EAS	801	mJ
Avalanche energy capability *	EAR	224	mJ
Drain power dissipation	P_D	40	W
		$T_a = 25^\circ C$	2.0
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

■ Package

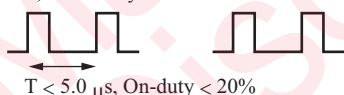
- Code
TO-220D-A1
- Pin Name
1: Gate
2: Drain
3: Source

■ Marking Symbol: K4208

■ Internal Connection



Note) *: Assurance of repetitive pulse. (Repetitive period $\leq 5 \mu s$ on-duty $\leq 20\%$)
But, it must stay within 40% of all that the time impressed pulse repetitively.



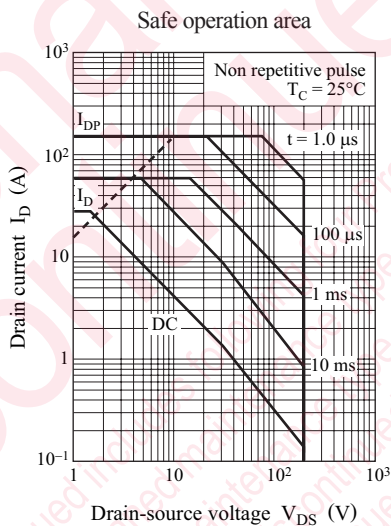
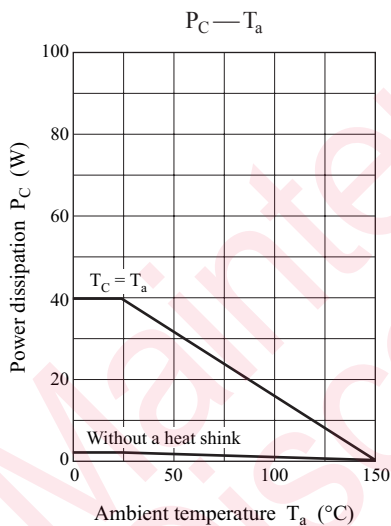
■ Electrical Characteristics $T_C = 25^\circ C \pm 3^\circ C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Drain-source surrender voltage	V_{DSS}	$I_D = 1$ mA, $V_{GS} = 0$	200			V	
Drain-source cutoff current	I_{DSS}	$V_{DS} = 160$ V, $V_{GS} = 0$			1.0	μA	
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 30$ V, $V_{DS} = 0$			± 1.0	μA	
Gate threshold voltage	V_{th}	$V_{DS} = 10$ V, $I_D = 1.0$ mA	2.5		4.5	V	
Drain-source ON resistance	$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 15.0$ A		43	52	m Ω	
Forward transfer conductance	$ Y_{fs} $	$V_{DS} = 10$ V, $I_D = 15.0$ A	12	22		S	
Short-circuit input capacitance (Common source)	C_{iss}	$V_{DS} = 2.5$ V, $V_{GS} = 0$, $f = 1$ MHz		1970		pF	
Short-circuit output capacitance (Common source)	C_{oss}				400		pF
Reverse transfer capacitance (Common source)	C_{rss}				85		pF
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 100$ V, $I_D = 15.0$ A $R_L \approx 6.7 \Omega$, $V_{GS} = 10$ V		32		ns	
Rise time	t_r				130		ns
Turn-off delay time	$t_{d(off)}$				170		ns
Fall time	t_f				88		ns

■ Electrical Characteristics (continued) $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

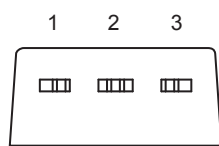
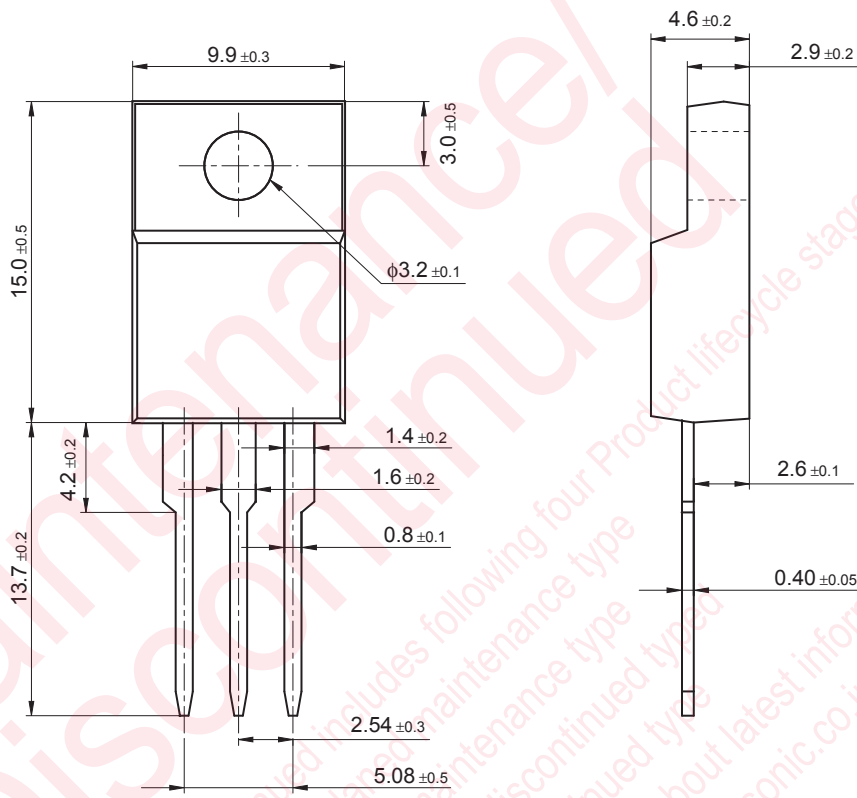
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode forward voltage	V_{DSF}	$I_{DR} = 30\text{ A}, V_{GS} = 0$			-1.5	V
Reverse recovery time	t_{rr}	$L = 230\ \mu\text{H}, V_{DD} = 100\text{ V}$		220		ns
Reverse recovery charge	Q_{rr}	$I_{DR} = 13.0\text{ A}, d_i/d_t = 100\text{ A}/\mu\text{s}$		1.1		nC
Gate charge load	Q_g	$V_{DD} = 100\text{ V}, I_D = 15.0\text{ A}, V_{GS} = 10\text{ V}$		66		nC
Gate-source charge	Q_{gs}			11		nC
Gate-drain charge	Q_{gd}			34		nC
Thermal resistance (ch-c)	$R_{th(ch-c)}$				3.13	$^\circ\text{C}/\text{W}$
Thermal resistance (ch-a)	$R_{th(j-a)}$				62.5	$^\circ\text{C}/\text{W}$

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



TO-220D-A1

Unit: mm



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